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AMENDMENTS TO THE CLAIMS

1. (Currently Amended) An apparatus for forming at least a portion of a semiconductor device, said apparatus comprising:
 - a reaction chamber for heating a substrate on which the semiconductor device is to be formed;
 - a first source for supplying a first treating gas to said reaction chamber;
 - a first pumping system coupled to said reaction chamber for maintaining said reaction chamber at a first vacuum pressure during the supplying of said first treating gas;
 - a second source for supplying a second treating gas to said reaction chamber;
 - a second pumping system coupled to said reaction chamber for maintaining said reaction chamber at a second vacuum pressure during the supplying of said second treating gas, said second vacuum pressure being lower than said first vacuum pressure; and,
 - a third pumping system coupled to said reaction chamber for transitioning said reaction chamber between said first vacuum pressure and said second vacuum pressure.
2. (Original) An apparatus according to claim 1, wherein said reaction chamber, said first source and said first pumping system form at least part of a Low Pressure Chemical Vapor Deposition (LPCVD) system.
3. (Original) An apparatus according to claim 2, wherein said reaction chamber, said second source and said second pumping system form at least part of an Ultra High Vacuum-Chemical Vapor Deposition (UHV-CVD) system.
4. (Original) An apparatus according to claim 1, further comprising a load-lock chamber coupled to said reaction chamber for transferring said substrate between said reaction

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